

Shantou Huashan Electronic Devices Co.,Ltd.

NPN SILICON TRANSISTOR

HBD241C

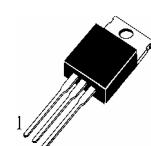
■ APPLICATIONS

Medium Power Linear And Switching Application.

■ ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

T_{stg}	Storage Temperature	-65~150°C
T_j	Junction Temperature	150°C
P_c	Collector Dissipation ($T_c=25^\circ\text{C}$)	40W
V_{CER}	Collector-Emitter Voltage	115V
V_{CEO}	Collector-Emitter Voltage	100V
V_{EBO}	Emitter-Base Voltage	5V
I_c	Collector Current (DC)	3A
I_c	Collector Current (Pulse)	5A
I_B	Base Current	1A

TO-220



- 1—Base, B
2—Collector, C
3—Emitter, E

■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

Symbol	Characteristics	Min	Typ	Max	Unit	Test Conditions
$BV_{CEO(SUS)}$	Collector-Emitter Sustaining Voltage	100			V	$I_C=30\text{mA}, I_B=0$
I_{CEO}	Collector Cut-off Current			300	nA	$V_{CE}=60\text{V}, I_B=0$
I_{EBO}	Emitter-Base Cutoff Current			1	mA	$V_{EB}=5\text{V}, I_C=0$
I_{CES}	Collector Cutoff Current			200	μA	$V_{CE}=100\text{V}, V_{BE}=0$
HFE (1)	DC Current Gain	25				$V_{CE}=4\text{V}, I_C=1\text{A}$
HFE (2)		10				$V_{CE}=4\text{V}, I_C=3\text{A}$
$V_{CE(sat)}$	Collector- Emitter Saturation Voltage			1. 2	V	$I_C=3\text{A}, I_B=0.6\text{A}$
$V_{BE(on)}$	Base- Emitter On Voltage			1. 8	V	$V_{CE}=4\text{V}, I_C=3\text{A},$